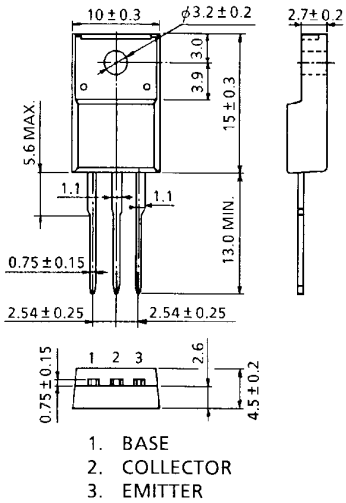
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1887

High-Current Switching Applications

Unit: mm

- Low collector saturation voltage: $V_{CE\ (sat)} = -0.4$ V (max) at $I_C = -5$ A



JEDEC	—
JEITA	SC-67
TOSHIBA	2-10R1A

Weight: 1.7 g (typ.)

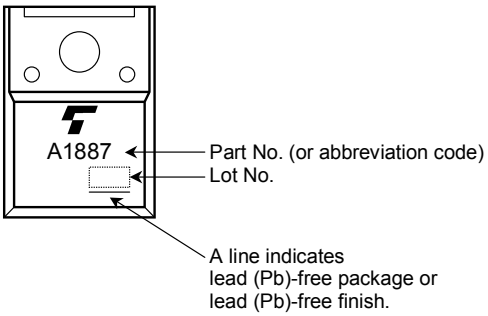
Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	−80	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage		V_{EBO}	−7	V
Collector current		I_C	−10	A
Collector power dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		25	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Electrical Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −70 V, I_E = 0	—	—	−1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −7 V, I_C = 0	—	—	−1	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = −10 mA, I_B = 0	−50	—	—	V
DC current gain	h_{FE}	V_{CE} = −1 V, I_C = −1 A	120	—	400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −5 A, I_B = −0.25 A	—	−0.2	−0.4	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C = −5 A, I_B = −0.25 A	—	−0.95	−1.4	V
Transition frequency	f_T	V_{CE} = −1 V, I_C = −1 A	—	45	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	215	—	pF

Marking



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